Introduction to Pixel Detectors

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Particle Physics School Colloquium - PPSMC

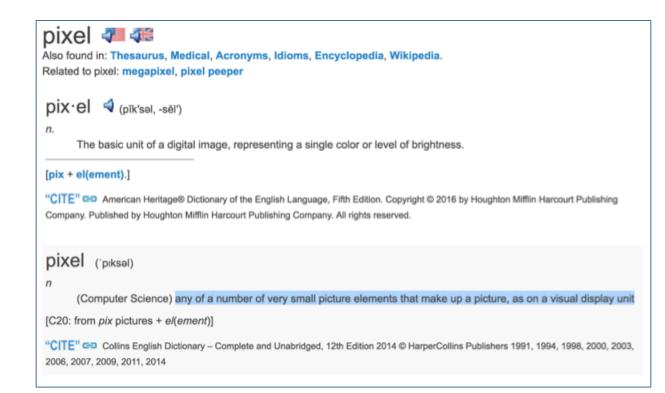




Overview



- 1. What is a pixel detector
- 2. How does a pixel detector work
- 3. How to make the sensor of a pixel detector
- 4. Applications of pixel detectors

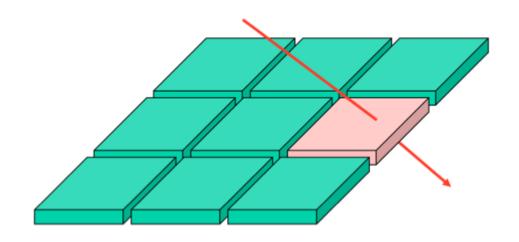


Part 2: Specific application: Development of pixel detectors for ATLAS (Natascha)

What is a Pixel Detector

Introduction





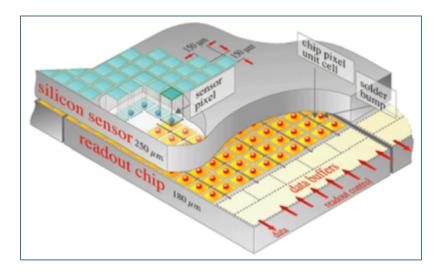
- a (solid state) detector which is segmented into 2-dimensional sensing elements
 - a charged particle or a gamma ray produces a signal by ionisation
 - pulse processing electronics amplify the signals and distinguish signals from noise
 - signal leads to true 2-dimensional spatial information (no ambiguities)

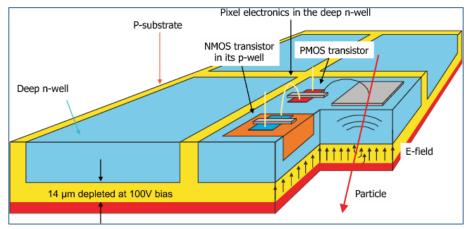
What is a Pixel Detector

Types of pixel detectors



- pixel detectors differ by
 - construction type
 - hybrid pixel detector: sensor volume and signal processing unit in two separate chips with 1:1 cell correspondence
 - monolithic detectors: signal processing electronics in the same device as the sensor volume
 - signal processing
 - single event readout (HEP), counting (x-ray), integrating (imaging)
 - sensor type
 - silicon, germanium, high-Z material, ...



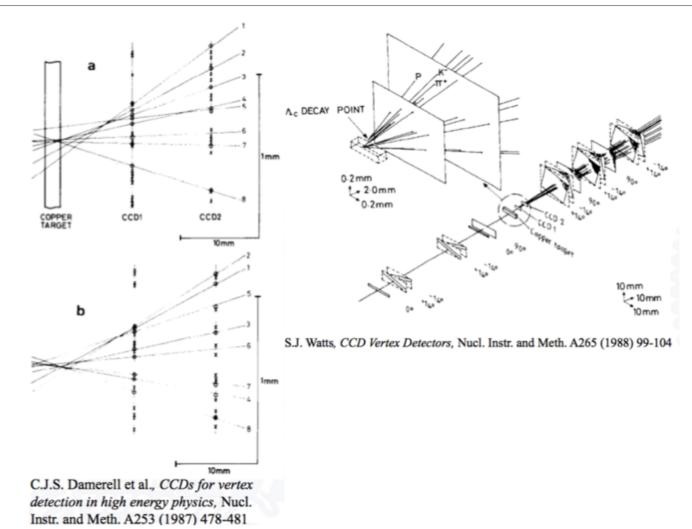


What is a Pixel Detector

Motivation and development in HEP



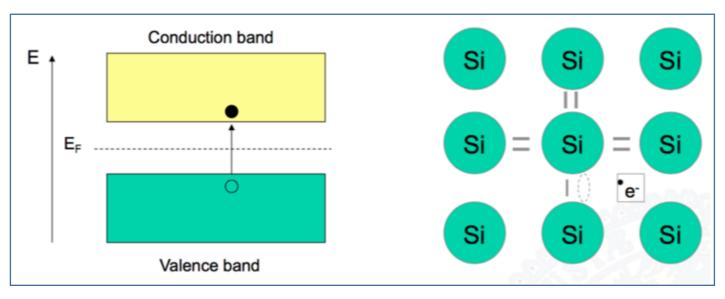
- pixel detectors are necessary to resolve the ambiguity in high multiplicity environments
 - typical task: tracking/vertexing close to the interaction point
- first application: reconstruct charm decays in NA32 (1982-1986)
- first hybrid pixel detector in 1990: WA97
- technology became available through huge success of semiconductor industry



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Semiconductor physics

- intrinsic silicon (at T=0K) has no free charge carriers
 - higher temperatures can lift charge carriers over the band-gap



$\frac{\int_{P} \Delta_{q} \geq \frac{1}{2} t}{\text{Max-Planck-Institut für Physik}}$

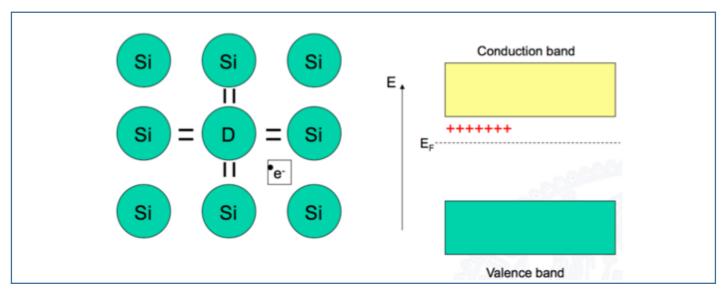
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 - donors provide one weakly bound extra electron -> energy levels close to the conduction band



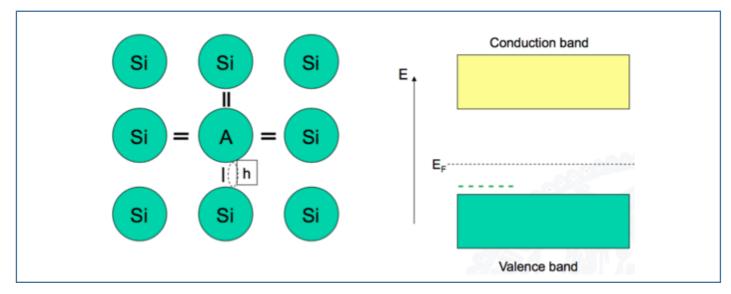
Max-Planck-Institut für Physik

Semiconductor physics

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 - donors provide one weakly bound extra electron -> energy levels close to the conduction band
 - acceptors provide one more energy level which can be filled by neighbouring electrons -> holes

Attention:

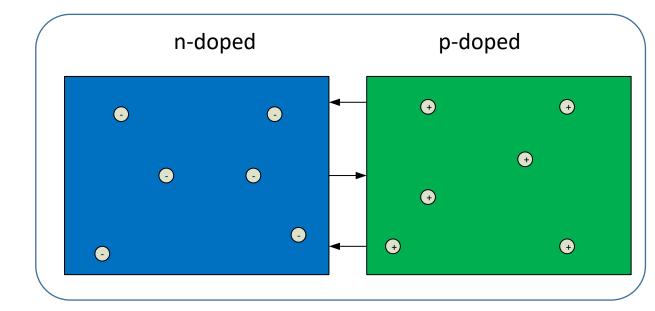
despite doped silicon having free charge carriers, it of course stays electrically neutral.





Simple Detector

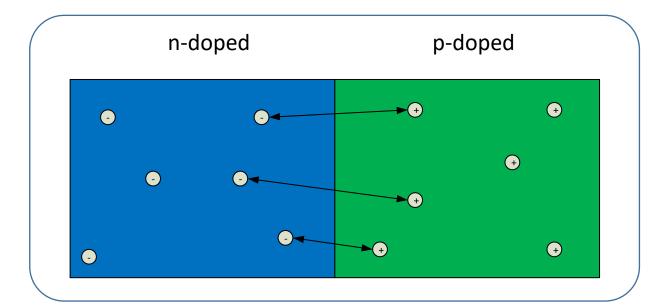
create a junction between n-type and p-type material



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Simple Detector

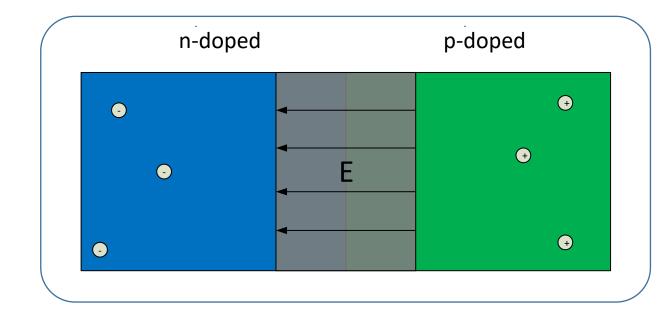
- create a junction between n-type and p-type material
- electron/hole pairs recombine in the border region
 - driving force: concentration gradient -> diffusion



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Simple Detector

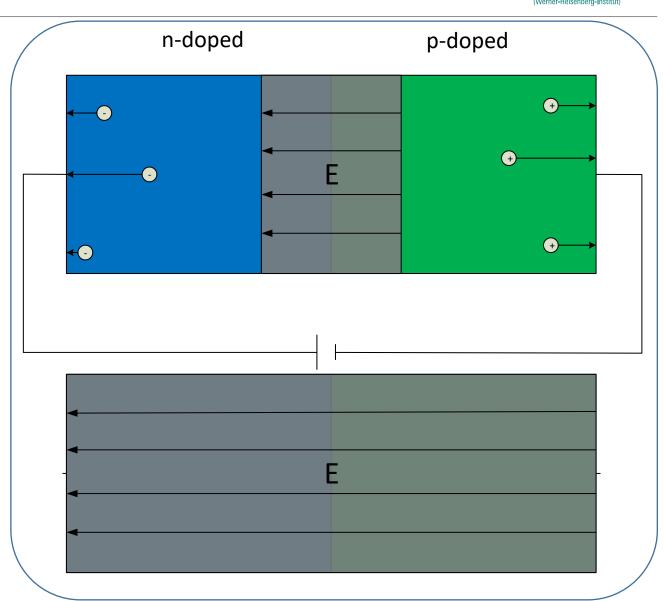
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- an electrical field builds up because the material is no longer electrical neutral
 - driving force: electrical field -> drift



$\frac{\Delta_{p} \cdot \Delta_{q} \geqslant \frac{1}{2} t}{\text{Max-Planck-Institut für Physik}}$

Simple Detector

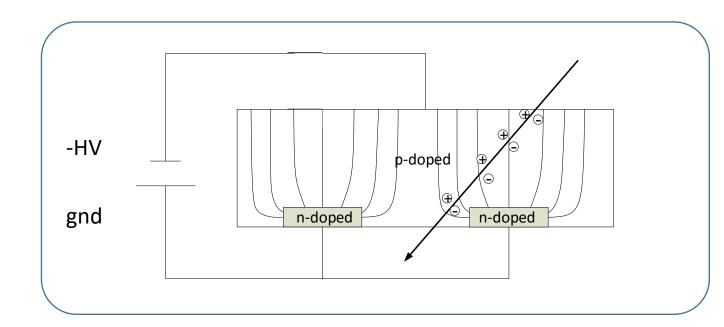
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 - driving force: concentration gradient -> diffusion
- an electrical field builds up because the material is no longer electrical neutral
 - driving force: electrical field -> drift
- an external voltage applied in reverse direction increases the electrical field, newly generated charge carriers will be removed from the device now





Translate this to a real sensor

- junction is created between p-doped bulk material and n-doped pixel implant
- the electrical field created by the applied bias voltage is used to separate electron/hole pairs created by through passing ionising particles

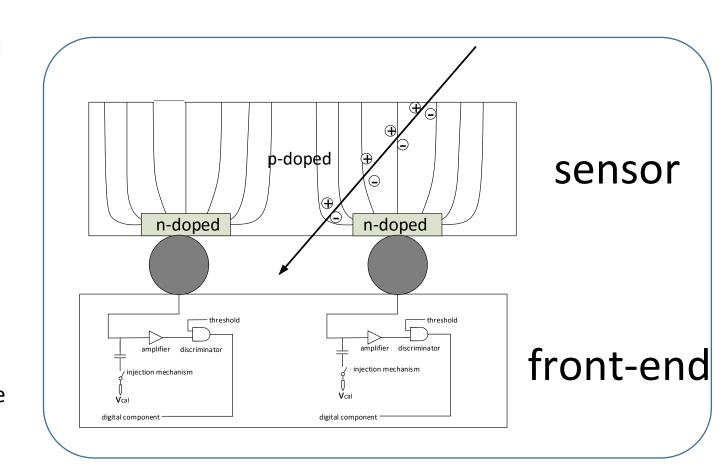




junction is created between p-doped bulk material and n-doped pixel implant

Translate this to a real sensor

- the electrical field created by the applied bias voltage is used to separate electron/hole pairs created by through passing ionising particles
- the signal is then read-out by the front-end chip: amplification, discrimination, digitalization, storage

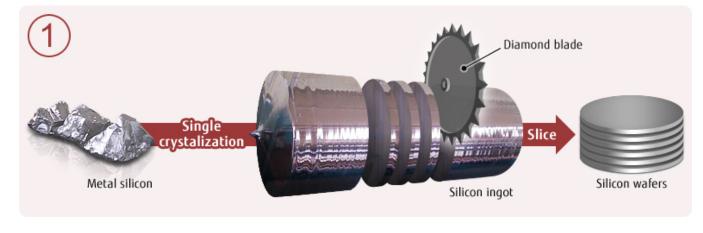


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Example: Silicon







- silicon dioxide (quarz -> sand) is the origin of all silicon sensors (and CPUs, GPUs, ASICs, FPGAs, ...)
- reducing the SiO₂ to pure silicon results in a polycrystalline structure
- following the path to a planar pixel sensor...

Technics to produce ingots:

- Czochalski: pull the monocrystalline silicon ingot out of molten silicon
- Float-Zone: melt a polycrystalline cylinder stepwise to get a monocrystalline ingot

Slicing the ingot with a diamond saw results in silicon wafers

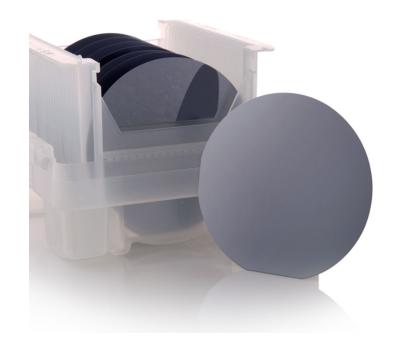


Processing silicon wafers - oxidation

Step 1: Oxidation

- the wafer is put in an oven at a high temperature (~1000°C)
- the surface atoms react with the oxygen and build an oxide layer on top
- longer exposure times lead to thicker oxide layers







Processing silicon wafers - photoresist

Step 2: Photo resist

- a liquid photo resist is put in the center of the wafer
- the wafer is rotated at a precise speed such that a homogeneous layer of defined thickness of photo resist stays on top of the wafer



Photoresist
Silicon Oxide
Silicon

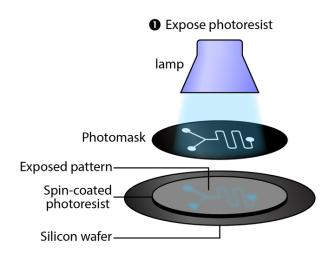


Processing silicon wafers - photolithography

Step 3: Photolithography

- expose the photoresist through a mask to a lamp
- not-exposed parts can be removed afterwards





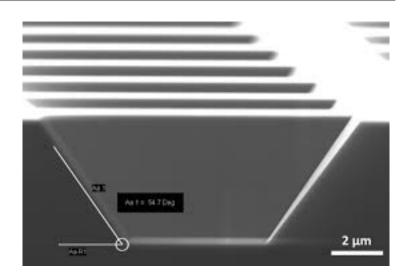


Processing silicon wafers - etching

Step 4: Etching

etch part of the previously grown oxide away



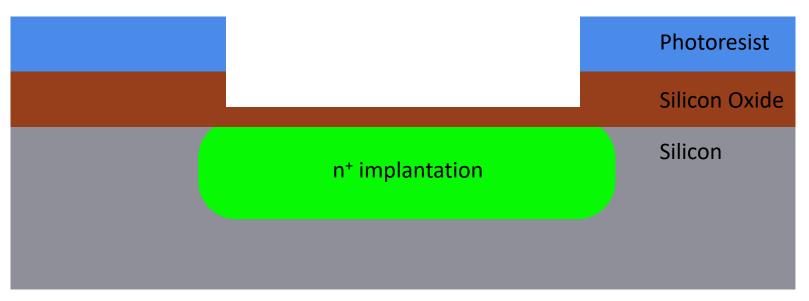


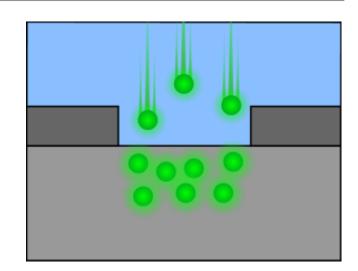


Processing silicon wafers – ion implantation

Step 5: Ion implantation

- doping atoms are ionized, accelerated and shot onto the wafer
- usually, another high-T step is applied to anneal the defects introduced into the silicon lattice by the high energetic ions



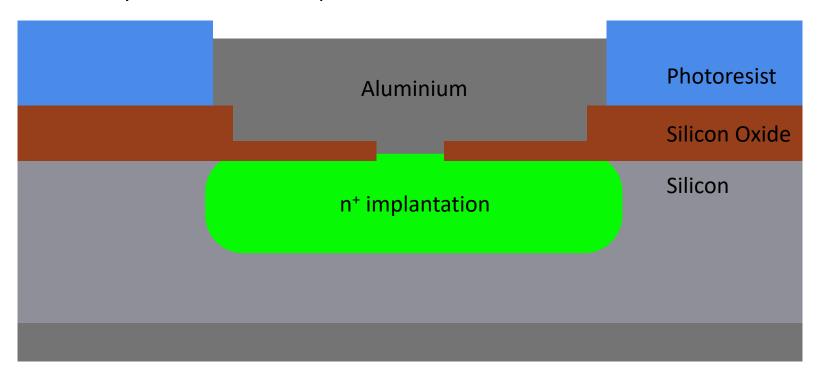


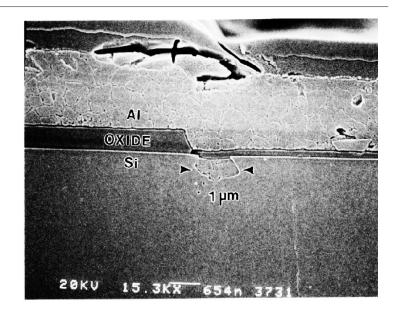


Processing silicon wafers – aluminium

Step 6: Aluminium deposition

- after some more higher order processing steps, a contact to the pixel implant is etched
- aluminium is sputtered on the surface using another photo resist mask
- another layer on the backside provides electrical contact



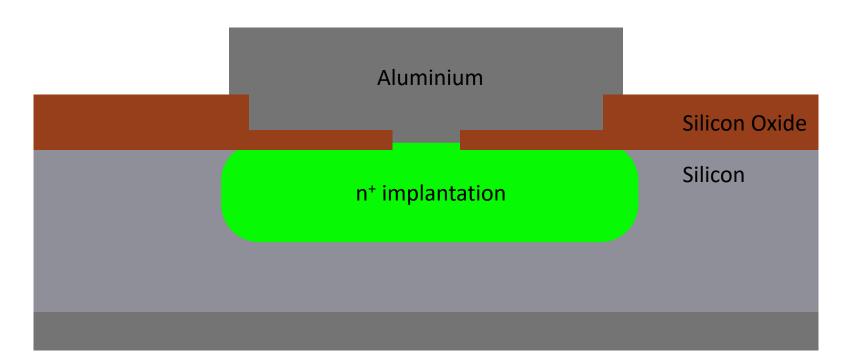


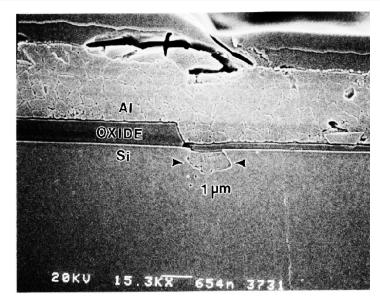


Processing silicon wafers – aluminium

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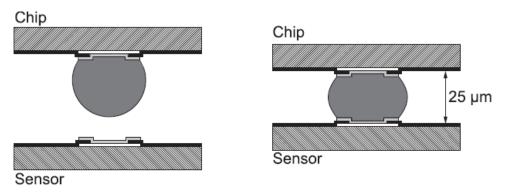


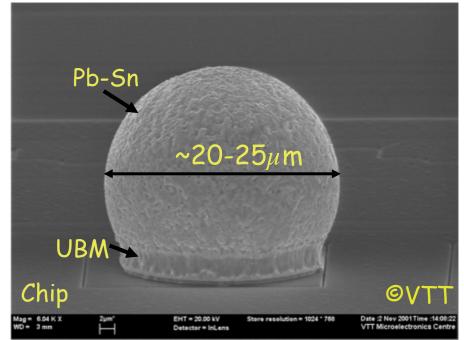


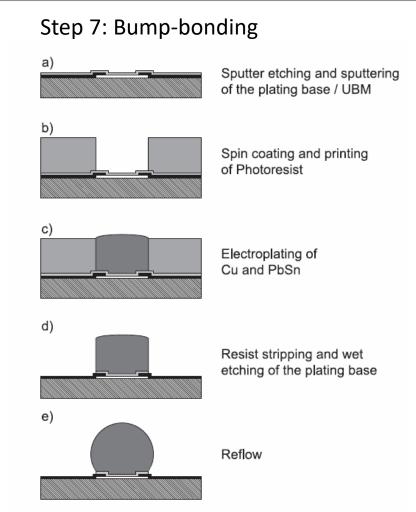
From a Sensor to a Detector

Solder bump-bonding





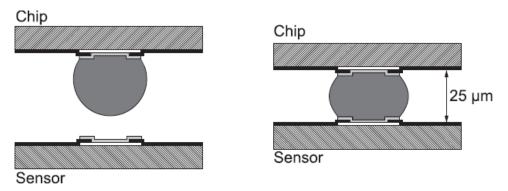


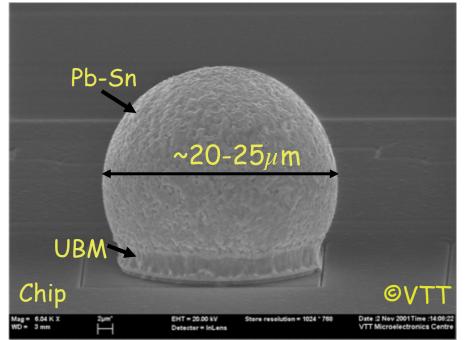


From a Sensor to a Detector

Solder bump-bonding

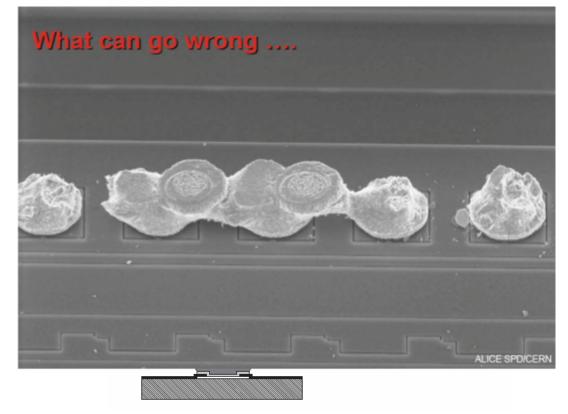






Step 7: Bump-bonding

Sputter etching and sputtering of the plating base / UBM



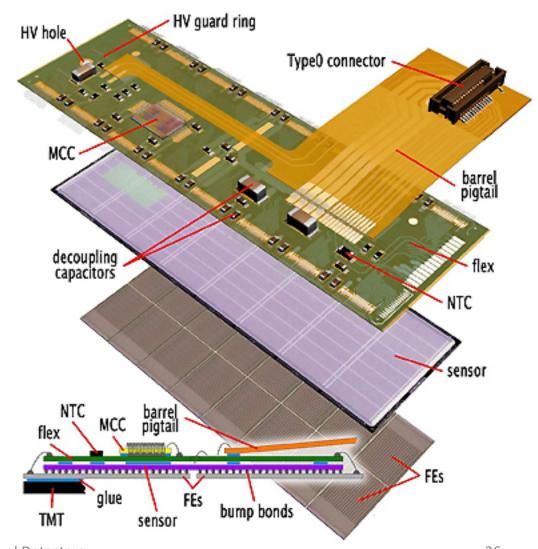
From a Sensor to a Detector

Putting the pieces together



Step 8: Module construction

- example: ATLAS pixel detector module
- 16 front-end chips flip-chipped to one sensor
- flex circuit print to connect the module to the offdetector read-out electronics via a cable
- module controller chip (MCC) combines the data streams of all front-end chips



Application of Pixel Detectors

MUON FILTER

Tracking detectors



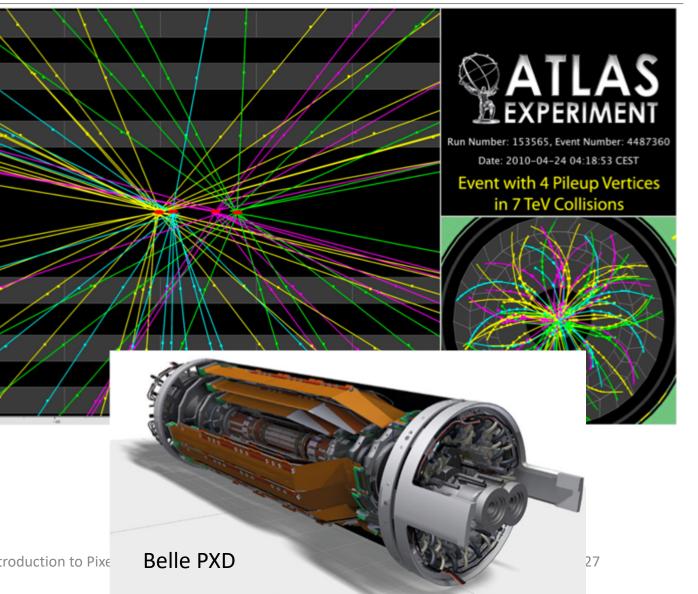
 pixel detectors are widely used as tracking detectors in HEP experiments

HMPID

ABSORBER

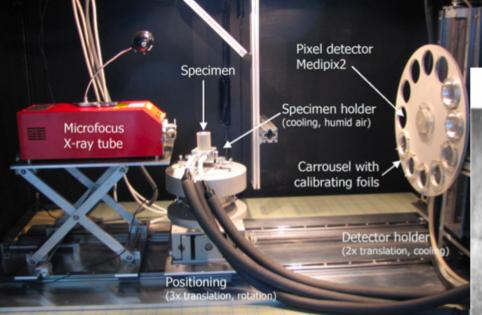
L3 MAGNET

 detect charged particle tracks to locate vertices and measure momentum

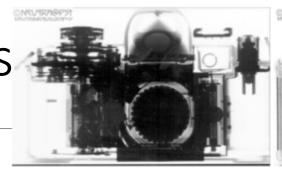


Application of Pixel Detectors

X-ray imaging



- pixel detectors can be tailored to detect all kinds of radiation, e.g. x-rays or neutron
- example: Medipix-2 read-out chip (HEP origin)

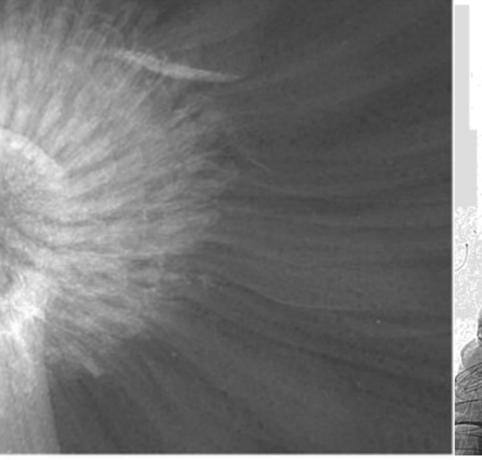


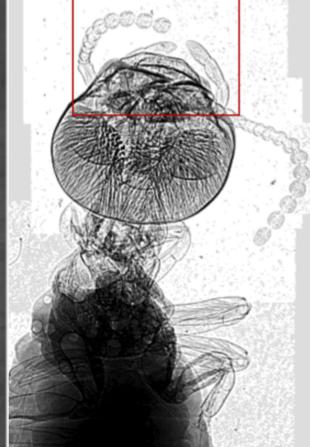


x-ray image

neutron image

Daisy blossom

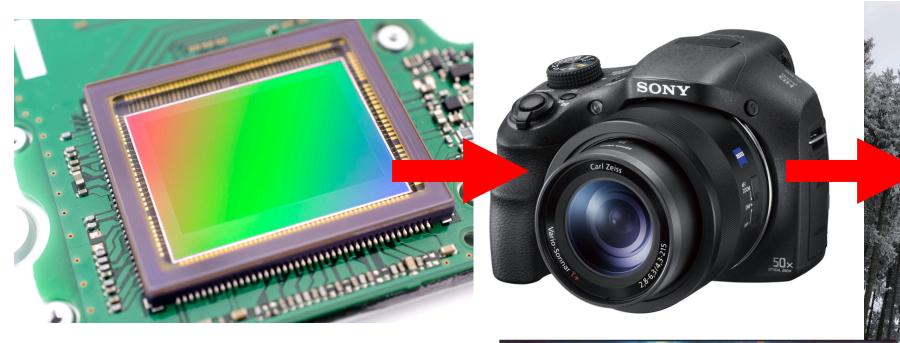




Application of Pixel Detectors

Optical imaging





- pixel detectors are used every day in all optical cameras from DSLR to phones
- also: imagining in astronomy from satellites to telescopes



The End

Backup

Title subtitle



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